

**MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA**

**High Voltage
Power Transistors
DPAK For Surface Mount Applications**

Designed for line operated audio output amplifier, switchmode power supply drivers and other switching applications.

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Lead Formed Version in 16 mm Tape and Reel ("-RL" Suffix)
- Electrically Similar to Popular TIP47, and TIP50
- 250 and 400 V (Min) — $V_{CEO(sus)}$
- 1 A Rated Collector Current

MAXIMUM RATINGS

Rating	Symbol	MJD47	MJD50	Unit
Collector-Emitter Voltage	V_{CEO}	250	400	Vdc
Collector-Base Voltage	V_{CB}	350	500	Vdc
Emitter-Base Voltage	V_{EB}	5		Vdc
Collector Current — Continuous Peak	I_C	1 2		Adc
Base Current	I_B	0.6		Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	15 0.12		Watts $W/^\circ\text{C}$
Total Power Dissipation* @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.56 0.0125		Watts $W/^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	8.33	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient*	$R_{\theta JA}$	80	$^\circ\text{C/W}$
Lead Temperature for Soldering Purpose	T_L	260	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage (1) ($I_C = 30 \text{ mAdc}, I_B = 0$)	MJD47 MJD50	$V_{CEO(sus)}$	250 400	—	Vdc
Collector Cutoff Current ($V_{CE} = 150 \text{ Vdc}, I_B = 0$) ($V_{CE} = 300 \text{ Vdc}, I_B = 0$)	MJD47 MJD50	I_{CEO}	— —	0.2 0.2	mAdc

* When surface mounted on minimum pad sizes recommended.
(1) Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

(continued)

**MJD47
MJD50**

**NPN SILICON
POWER TRANSISTORS
1 AMPERE
250, 400 VOLTS
15 WATTS**

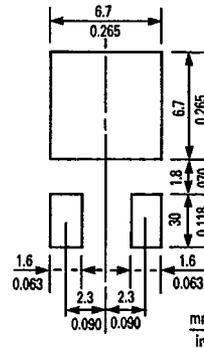


CASE 369A-04



CASE 369-03

**MINIMUM PAD SIZES
RECOMMENDED FOR
SURFACE MOUNTED
APPLICATIONS**



ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS — continued				
Collector Cutoff Current ($V_{CE} = 350\text{ Vdc}, V_{BE} = 0$) ($V_{CE} = 500\text{ Vdc}, V_{BE} = 0$)	I_{CES}	—	0.1	mAdc
	MJD47 MJD50	—	0.1	
Emitter Cutoff Current ($V_{BE} = 5\text{ Vdc}, I_C = 0$)	I_{EBO}	—	1	mAdc
ON CHARACTERISTICS (1)				
DC Current Gain ($I_C = 0.3\text{ Adc}, V_{CE} = 10\text{ Vdc}$) ($I_C = 1\text{ Adc}, V_{CE} = 10\text{ Vdc}$)	h_{FE}	30 10	150 —	—
Collector-Emitter Saturation Voltage ($I_C = 1\text{ Adc}, I_B = 0.2\text{ Adc}$)	$V_{CE(sat)}$	—	1	Vdc
Base-Emitter On Voltage ($I_C = 1\text{ Adc}, V_{CE} = 10\text{ Vdc}$)	$V_{BE(on)}$	—	1.5	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain — Bandwidth Product ($I_C = 0.2\text{ Adc}, V_{CE} = 10\text{ Vdc}, f = 2\text{ MHz}$)	f_T	10	—	MHz
Small-Signal Current Gain ($I_C = 0.2\text{ Adc}, V_{CE} = 10\text{ Vdc}, f = 1\text{ kHz}$)	h_{fe}	25	—	—

(1) Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS

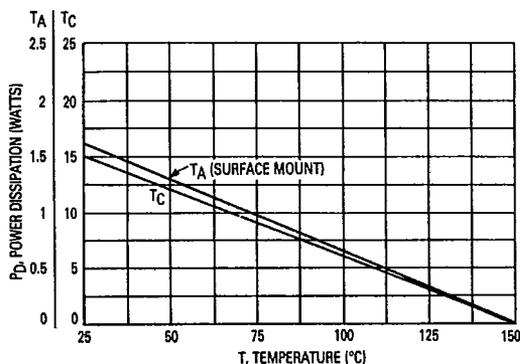


Figure 1. Power Derating

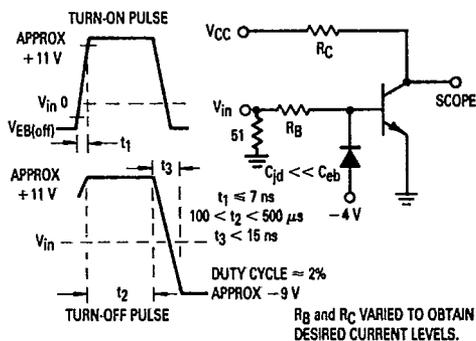


Figure 2. Switching Time Equivalent Circuit

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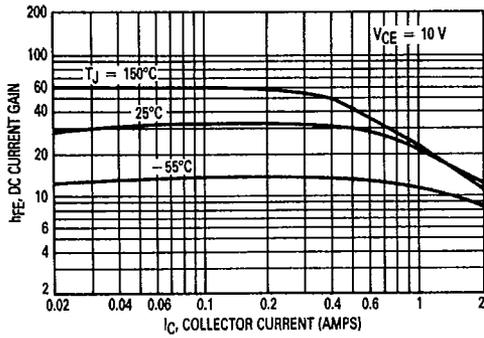


Figure 3. DC Current Gain

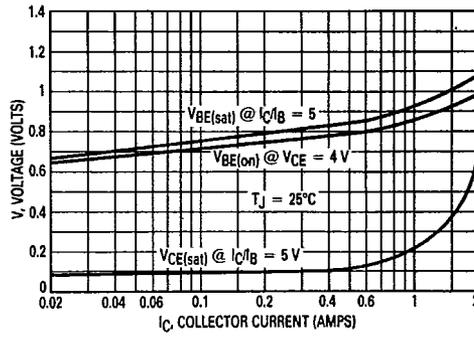


Figure 4. "On" Voltages

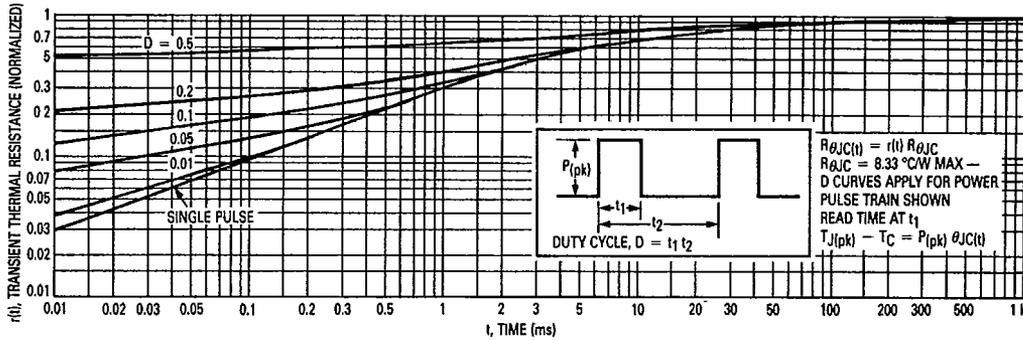


Figure 5. Thermal Response

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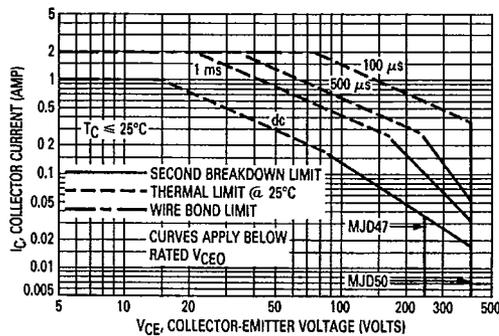


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

T-33-07

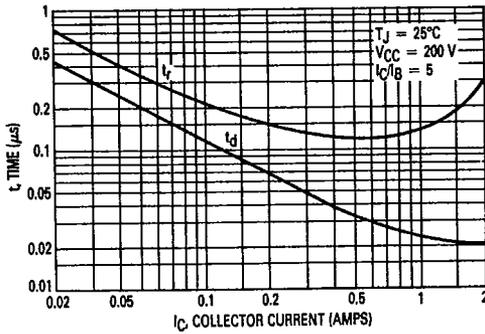


Figure 7. Turn-On Time

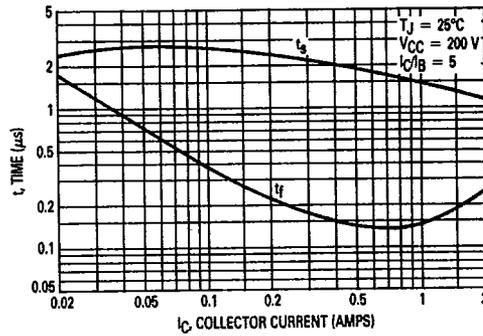


Figure 8. Turn-Off Time

OUTLINE DIMENSIONS

CASE 369-03

STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	5.97	6.22	0.235	0.245
B	6.35	6.73	0.250	0.265
C	2.19	2.38	0.086	0.094
D	0.54	0.88	0.021	0.035
E	0.97	1.06	0.038	0.042
G	2.29 BSC		0.090 BSC	
J	0.46	0.58	0.018	0.023
K	8.89	9.65	0.350	0.380
L	0.89	1.27	0.035	0.050
S	5.21	5.46	0.205	0.215
V	0.77	1.14	0.030	0.045
W	0.84	0.94	0.033	0.037
V	1.51	2.28	0.075	0.090

NOTES:
 1. SURFACE "T" IS BOTH A DATUM AND A MOUNTING SURFACE.
 2. POSITIONAL TOLERANCE FOR "D" DIAMETER: $\pm 0.13 (0.005) \text{ } \textcircled{T}$
 3. DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982
 4. CONTROLLING DIMENSION INCH

CASE 369A-04

STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	5.97	6.22	0.235	0.245
B	6.35	6.73	0.250	0.265
C	2.19	2.38	0.086	0.094
D	0.66	0.88	0.027	0.035
E	0.97	1.06	0.038	0.042
F	0.64	0.80	0.025	0.032
G	4.58 BSC		0.180 BSC	
H	2.29 BSC		0.090 BSC	
J	0.46	0.58	0.018	0.023
K	2.59	2.80	0.102	0.111
L	0.89	1.27	0.035	0.050
S	5.21	5.46	0.205	0.215
U	0.51	—	0.020	—
V	0.77	1.14	0.030	0.045
W	0.84	0.94	0.033	0.037
Y	4.32	—	0.170	—
Z	3.69	—	0.146	—

NOTES:
 1. SURFACE "T" IS BOTH A DATUM AND A MOUNTING SURFACE.
 2. POSITIONAL TOLERANCE FOR "D" DIAMETER: $\pm 0.13 (0.005) \text{ } \textcircled{T}$
 3. DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982
 4. CONTROLLING DIMENSION INCH

Case 369-03 may be ordered by adding a "-1" suffix to the device title (i.e. MJD47-1)

